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Kind regards,

Team Nexperia

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

Rev. 4 — 6 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview
		0.0.0.0.0

Type number	Package		NPN/PNP PNP/PNP Package		U
	NXP	JEITA	complement	complement	configuration
PEMH13	SOT666	-	PEMD13	PEMB13	ultra small and flat lead
PUMH13	SOT363	SC-88	PUMD13	PUMB13	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	



- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

| | 2 3 *sym063*

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

Table 4. Ordering information				
Type number	Package			
	Name	Description	Version	
PEMH13	-	plastic surface-mounted package; 6 leads	SOT666	
PUMH13	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMH13	21
PUMH13	H0*

[1] * = placeholder for manufacturing site code

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

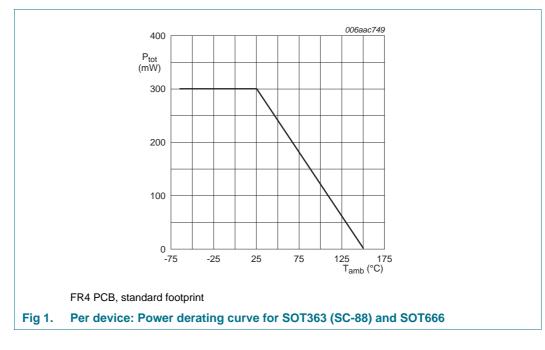
5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	stor					
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
VI	input voltage					
	positive			-	+30	V
	negative			-	-5	V
lo	output current			-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PEMH13 (SOT666)		[1][2]	-	200	mW
	PUMH13 (SOT363)		<u>[1]</u>	-	200	mW
Per device	;					
P _{tot}	total power dissipation	$T_{amb} \leq 25 ~^{\circ}C$				
	PEMH13 (SOT666)		[1][2]	-	300	mW
	PUMH13 (SOT363)		<u>[1]</u>	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω



Thermal characteristics 6.

<u> </u>	-	A 11/1		_		
Symbol	Parameter	Conditions	Mir	п Тур	Max	Unit
Per transi	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH13 (SOT666)		<u>[1][2]</u>	-	625	K/W
	PUMH13 (SOT363)		<u>[1]</u> _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH13 (SOT666)		<u>[1][2]</u> _	-	417	K/W
	PUMH13 (SOT363)		<u>[1]</u> _	-	417	K/W

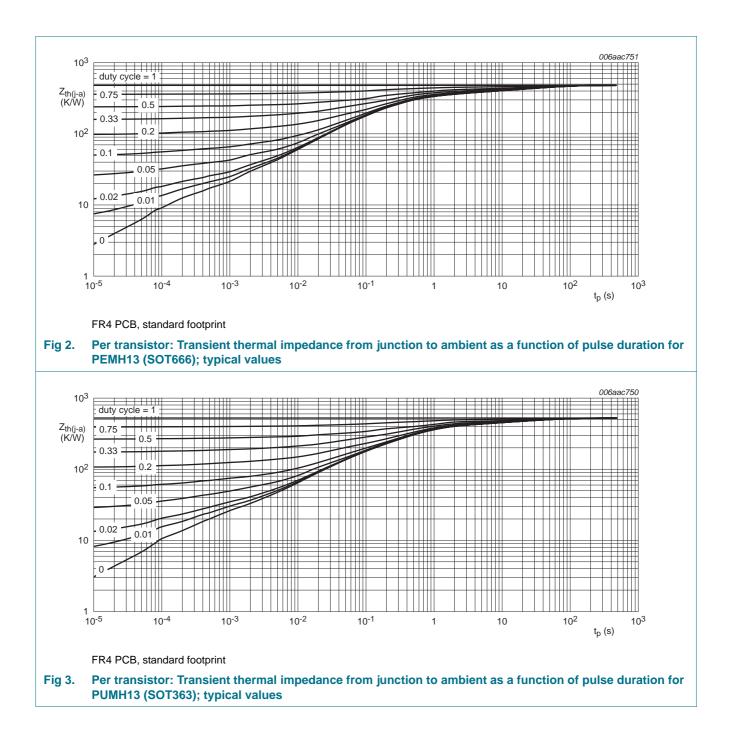
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMH13_PUMH13

PEMH13; PUMH13

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω



7. Characteristics

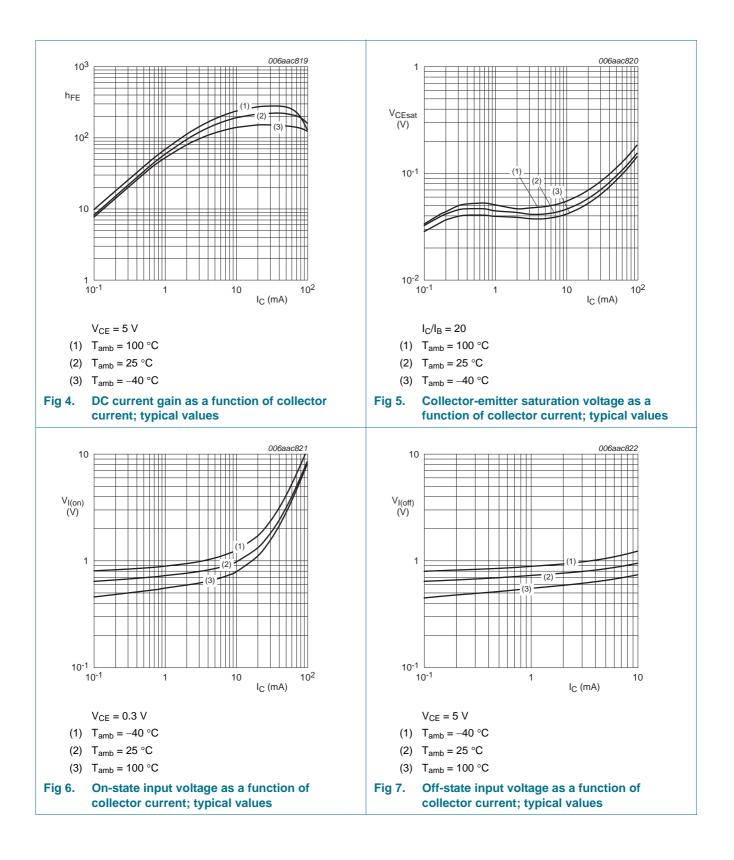
Table 8. $T_{amb} = 25$	Characteristics 5 °C unless otherwise spe	cified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μΑ
	current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	170	μA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}$	-	-	100	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A	-	0.6	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	1.3	0.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \; V; I_E = i_e = 0 \; A; \\ f = 1 \; MHz \end{array}$	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	<u>[1]</u> _	230	-	MHz

[1] Characteristics of built-in transistor

PEMH13_PUMH13 Product data sheet

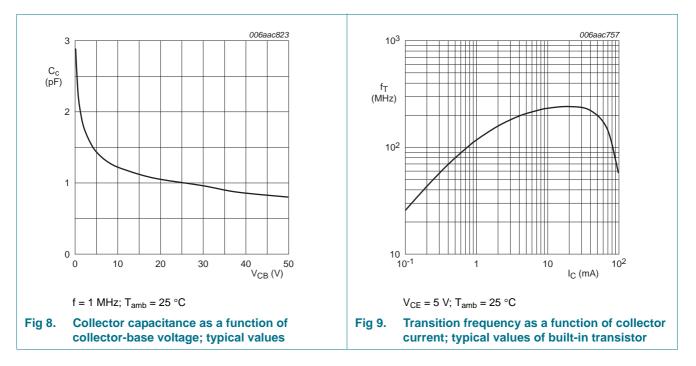
PEMH13; PUMH13

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω



PEMH13; PUMH13

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

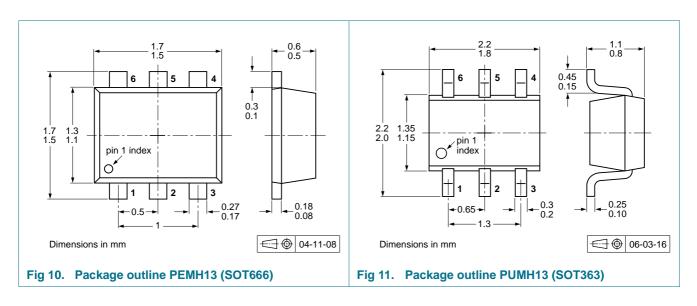


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMH13_PUMH13

10. Packing information

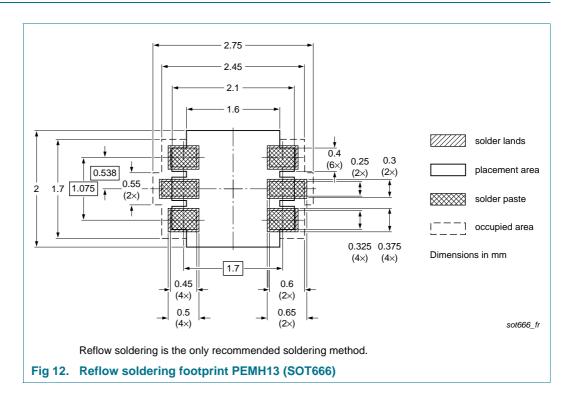
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

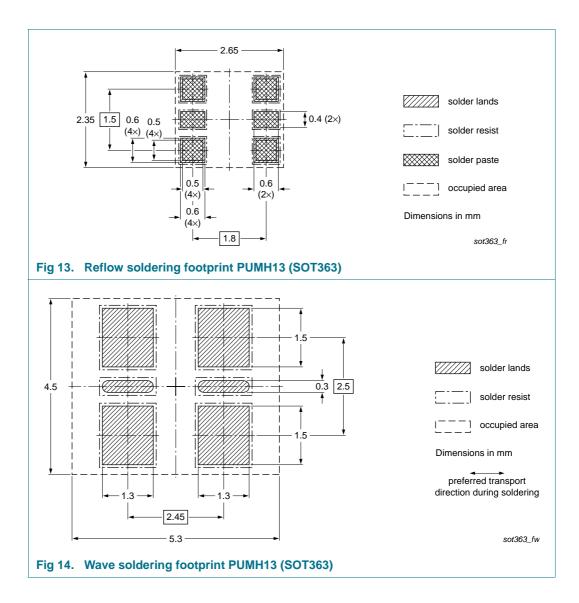
Туре	Package	Package Description			Packing quantity			
number				3000	4000	8000	10000	
PEMH13	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-	
		4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMH13	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165	

- [1] For further information and the availability of packing methods, see <u>Section 14</u>.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering



NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω



PEMH13_PUMH13
Product data shee

12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMH13_PUMH13 v.4	20111206	Product data sheet	-	PEMH13_PUMH13 v.3		
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	• Legal texts have been adapted to the new company name where appropriate.					
	Section 1 "Product profile": updated					
	Section 4 "I	Marking": updated				
	• Figure 1 to 9: added					
	 <u>Section 5 "Limiting values"</u>: updated 					
	 <u>Section 6 "Thermal characteristics"</u>: updated 					
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 					
	<u>Section 8 "Test information"</u> : added					
	 <u>Section 9 "Package outline"</u>: superseded by minimized package outline drawing 					
	Section 10 "Packing information": added					
	 <u>Section 11 "Soldering"</u>: added 					
	Section 13	"Legal information": updated				
PEMH13_PUMH13 v.3	20040414	Product data sheet	-	PEMH13_PUMH13 v.2		
PEMH13_PUMH13 v.2	20031107	Product specification	-	PEMH13 v.1		
PEMH13 v.1	20011213	Preliminary specification	-	-		

PEMH13_PUMH13

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMH13_PUMH13

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

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PEMH13; PUMH13

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

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